

N-channel TrenchMOS logic level FET Rev. 02 — 1 February 2011

Product data sheet

1. **Product profile**

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 185 °C rating

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 185 °C	-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	47	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	167	W
Static ch	aracteristics					
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C	-	24	28	mΩ
	resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 9; see Figure 13	-	25	30	mΩ
Avalanch	ne ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 47 \text{ A}; \text{V}_{\text{sup}} \leq 100 \text{ V}; \\ R_{GS} &= 50 \Omega; \text{V}_{GS} = 5 \text{ V}; \\ T_{j(\text{init})} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $	-	-	150	mJ
Dynamic	characteristics					
Q _{GD}	gate-drain charge		-	13	-	nC

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

[1] It is not possible to make a connection to pin 2 of the SOT428 package.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK9230-100B	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 185 °C	-	100	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-15	15	V
I _D	drain current	$T_{mb} = 100 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 1}}{100 \text{ C}}$	-	33	А
		T_{mb} = 25 °C; V_{GS} = 5 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	47	A
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed; t _p ≤ 10 μs; see <u>Figure 3</u>	-	185	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	167	W
T _{stg}	storage temperature		-55	185	°C
Tj	junction temperature		-55	185	°C
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	47	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	185	Α
Avalanche r	uggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_D = 47 \text{ A}; \ V_{sup} \leq 100 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 5 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped \end{array}$	-	150	mJ

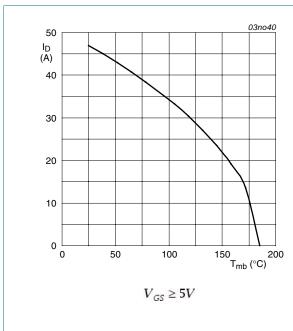
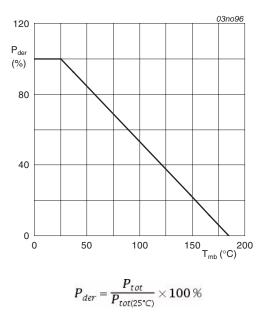
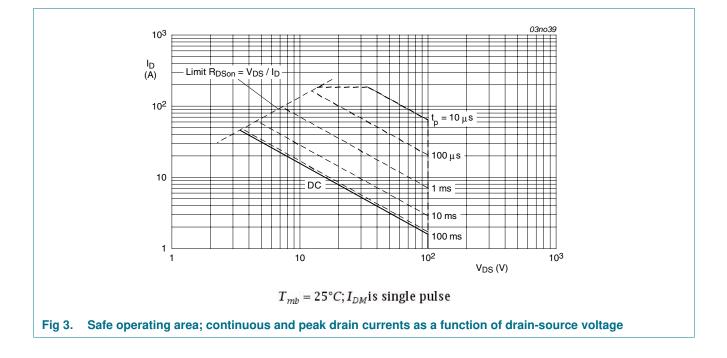


Fig 1. Continuous drain current as a function of mounting base temperature





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Thermal characteristics 5.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.95	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	71.4	-	K/W

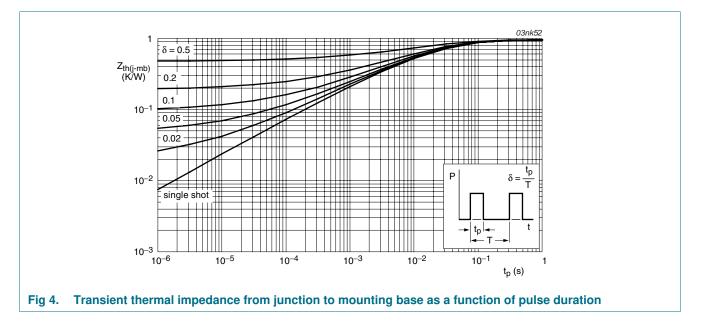
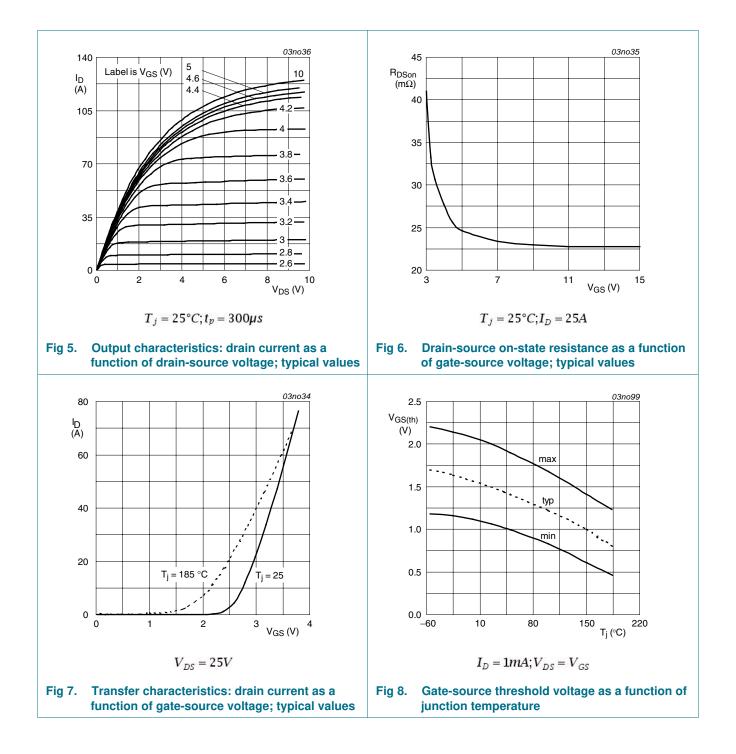


Table 5. **Thermal characteristics**

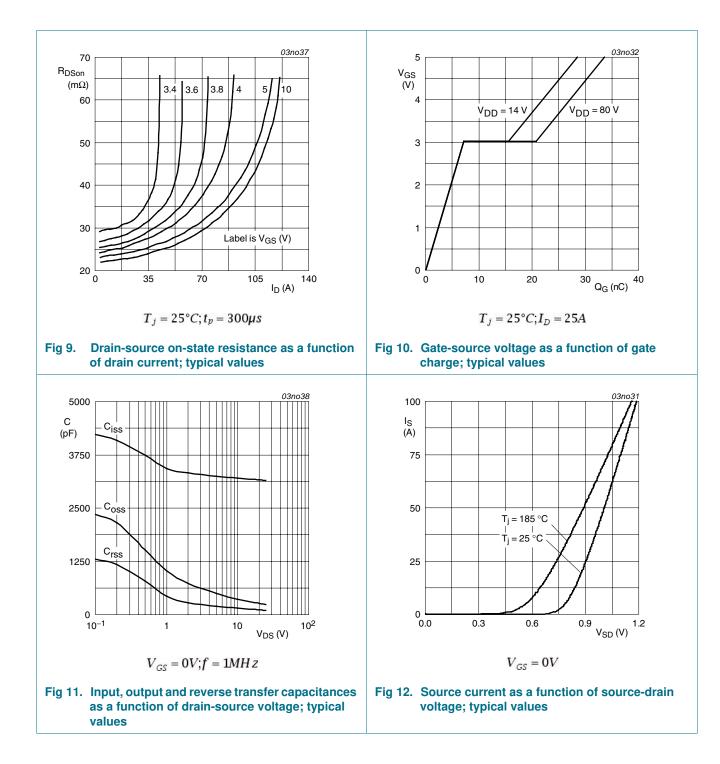
6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown	I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C	89	-	-	V
	voltage	I _D = 0.25 mA; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 185 \text{ °C};$ see Figure 8	0.4	-	-	V
		$\label{eq:ID} \begin{split} I_D = 1 \mbox{ mA; } V_{DS} = V_{GS}; T_j = 25 \mbox{ °C}; \\ see \mbox{ Figure 8} \end{split}$	1.1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 8</u>	-	-	2.3	V
DSS	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 185 °C	-	-	500	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA
I _{GSS}	gate leakage current	V_{GS} = 15 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -15 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon} drain-source on-state resistance		V _{GS} = 5 V; I _D = 25 A; T _j = 185 °C; see <u>Figure 9</u> ; see <u>Figure 13</u>	-	-	78	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	24	28	mΩ
		V_{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	33	mΩ
	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 13</u>	-	25	30	mΩ	
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$	-	33	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{10}$	-	7	-	nC
Q _{GD}	gate-drain charge		-	13	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	2854	3805	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 11</u>	-	232	278	pF
C _{rss}	reverse transfer capacitance		-	81	110	pF
d(on)	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω ; V_{GS} = 5 V;	-	30	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; \ T_j = 25 \ ^{\circ}C$	-	86	-	ns
d(off)	turn-off delay time		-	96	-	ns
t _f	fall time		-	46	-	ns
L _D	internal drain inductance	measured from drain to center of die ; $T_{j}=25\ ^{\circ}\text{C}$	-	2.5	-	nH
-S	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-drai	n diode					
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 12</u>	-	0.85	1.2	V
rr	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ d}_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	114	-	ns
Qr	recovered charge	V _{GS} = -10 V; V _{DS} = 30 V; T _j = 25 °C	-	196	-	nC

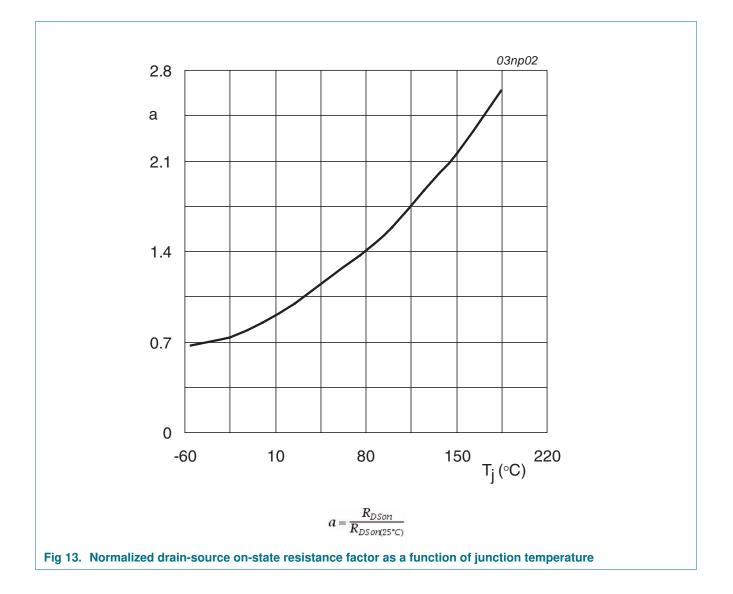
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7. Package outline

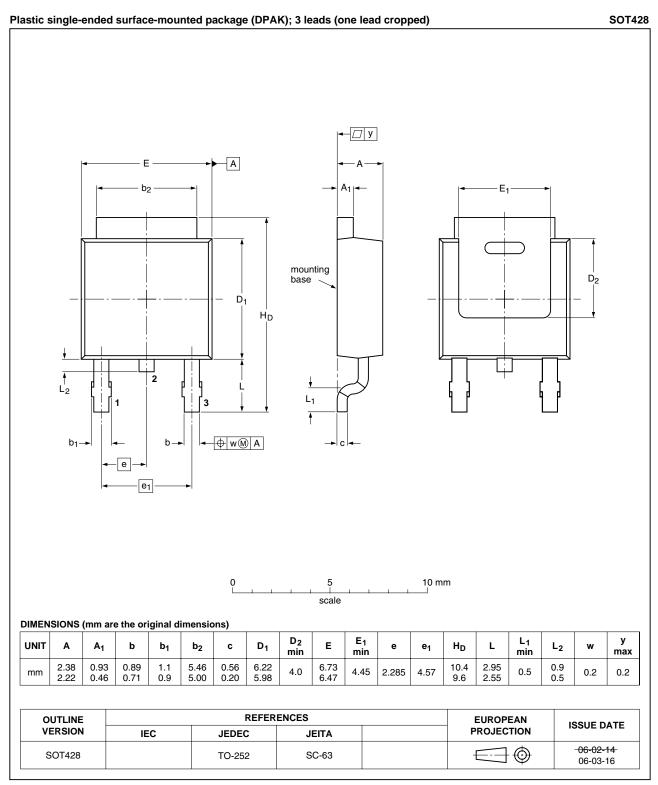


Fig 14. Package outline SOT428 (DPAK)

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8. Revision history

Table 7. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9230-100B v.2	20110201	Product data sheet	-	BUK9230_100B v.1
Modifications:	 The format of of NXP Semic 	this data sheet has been rec conductors.	designed to comply with	the new identity guidelines
	 Legal texts had 	we been adapted to the new	company name where	appropriate.
BUK9230_100B v.1	20040122	Product data	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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